PDTD123E series

NPN 500 mA, 50 V resistor-equipped transistors; R1 = 2.2 kΩ, R2 = 2.2 kΩ

Rev. 02 — 16 November 2009 Product data sheet

1. Product profile

1.1 General description

500 mA NPN Resistor-Equipped Transistors (RET) family.

Table 1. Product overview

Type number	Package			PNP complement
	NXP	JEITA	JEDEC	
PDTD123EK	SOT346	SC-59A	TO-236	PDTB123EK
PDTD123ES[1]	SOT54	SC-43A	TO-92	PDTB123ES
PDTD123ET	SOT23	-	TO-236AB	PDTB123ET

[1] Also available in SOT54A and SOT54 variant packages (see Section 2).

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- 500 mA output current capability
- Reduces component count
- Reduces pick and place costs
- ±10 % resistor ratio tolerance

1.3 Applications

- Digital application in automotive and industrial segments
- Controlling IC inputs
- Cost saving alternative for BC817 series in digital applications
- Switching loads

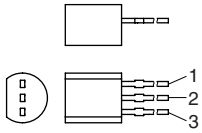
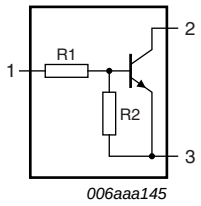
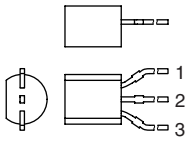
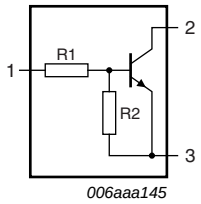
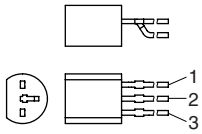
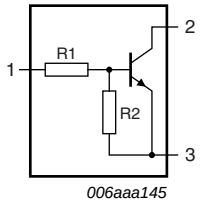
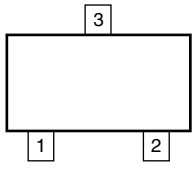
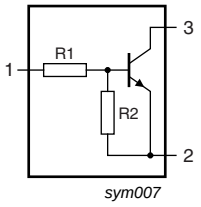
1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
I_O	output current (DC)		-	-	500	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		0.9	1.0	1.1	

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
SOT54			
1	input (base)	 001aab347	 006aaa145
2	output (collector)		
3	GND (emitter)		
SOT54A			
1	input (base)	 001aab348	 006aaa145
2	output (collector)		
3	GND (emitter)		
SOT54 variant			
1	input (base)	 001aab447	 006aaa145
2	output (collector)		
3	GND (emitter)		
SOT23, SOT346			
1	input (base)	 006aaa144	 sym007
2	GND (emitter)		
3	output (collector)		

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PDTD123EK	SC-59A	plastic surface mounted package; 3 leads	SOT346
PDTD123ES[1]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54
PDTD123ET	-	plastic surface mounted package; 3 leads	SOT23

[1] Also available in SOT54A and SOT54 variant packages (see Section 2 and Section 9).

4. Marking

Table 5. Marking codes

Type number	Marking code[1]
PDTD123EK	E3
PDTD123ES	D123ES
PDTD123ET	*7T

[1] * = -: made in Hong Kong
* = p: made in Hong Kong
* = t: made in Malaysia
* = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	50	V
V_{EBO}	emitter-base voltage	open collector		-	10	V
V_I	input voltage					
	positive			-	+12	V
	negative			-	−10	V
I_O	output current (DC)			-	500	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]			
	SOT346			-	250	mW
	SOT54			-	500	mW
	SOT23			-	250	mW
T_{stg}	storage temperature			−65	+150	°C
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			−65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]				
	SOT346			-	-	500	K/W
	SOT54			-	-	250	K/W
	SOT23			-	-	500	K/W

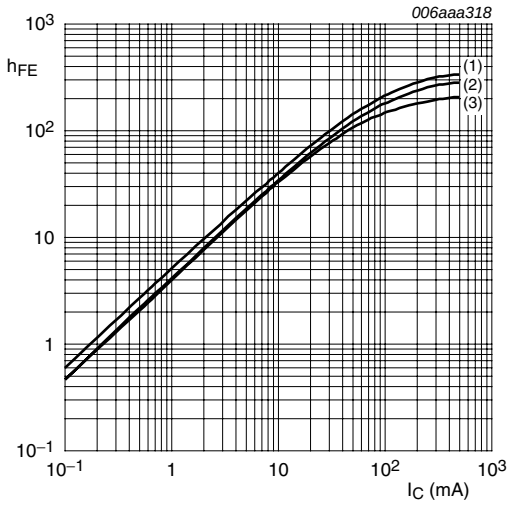
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	V_{CB} = 40 V; I_E = 0 A	-	-	100	nA
		V_{CB} = 50 V; I_E = 0 A	-	-	100	nA
I_{CEO}	collector-emitter cut-off current	V_{CE} = 50 V; I_B = 0 A	-	-	0.5	μA
I_{EBO}	emitter-base cut-off current	V_{EB} = 5 V; I_C = 0 A	-	-	2	mA
h_{FE}	DC current gain	V_{CE} = 5 V; I_C = 50 mA	40	-	-	
V_{CEsat}	collector-emitter saturation voltage	I_C = 50 mA; I_B = 2.5 mA	-	-	0.3	V
$V_{I(off)}$	off-state input voltage	V_{CE} = 5 V; I_C = 100 μA	0.6	1.1	1.8	V
$V_{I(on)}$	on-state input voltage	V_{CE} = 0.3 V; I_C = 20 mA	1.0	1.5	2.0	V
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		0.9	1.0	1.1	
C_c	collector capacitance	V_{CB} = 10 V; I_E = i_e = 0 A; f = 100 MHz	-	7	-	pF



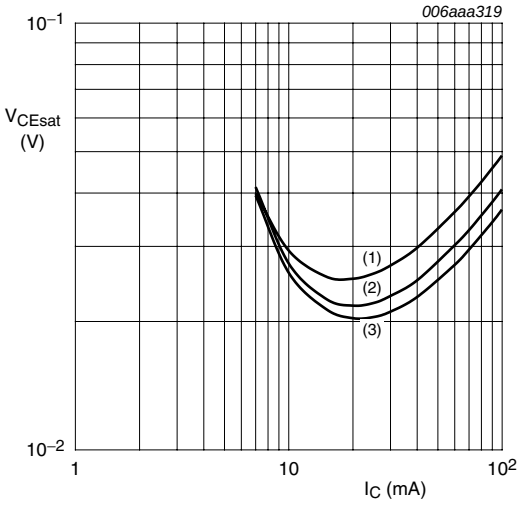
V_{CE} = 5 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 1. DC current gain as a function of collector current; typical values



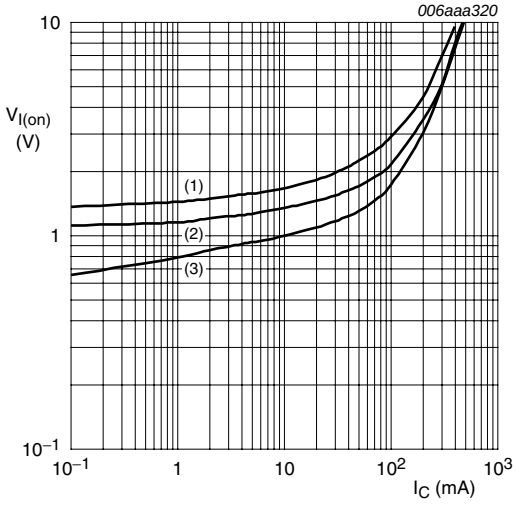
I_C/I_B = 20

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values



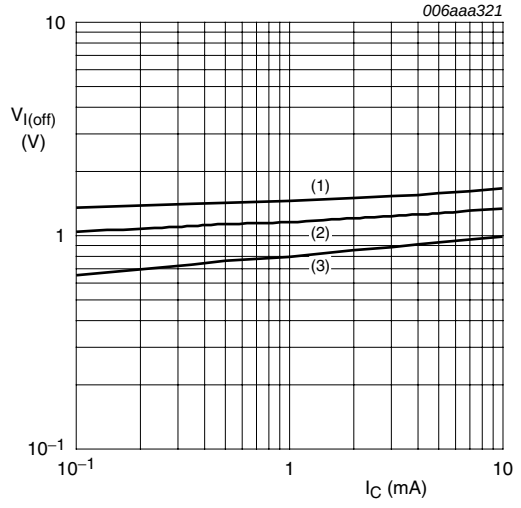
V_{CE} = 0.3 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 3. On-state input voltage as a function of collector current; typical values



V_{CE} = 5 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 4. Off-state input voltage as a function of collector current; typical values

8. Package outline

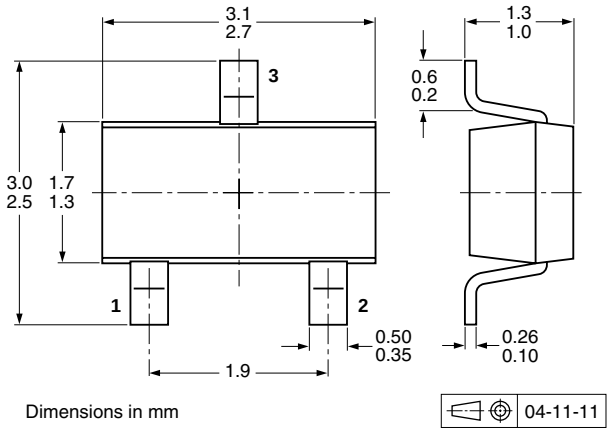


Fig 5. Package outline SOT346 (SC-59A/TO-236)

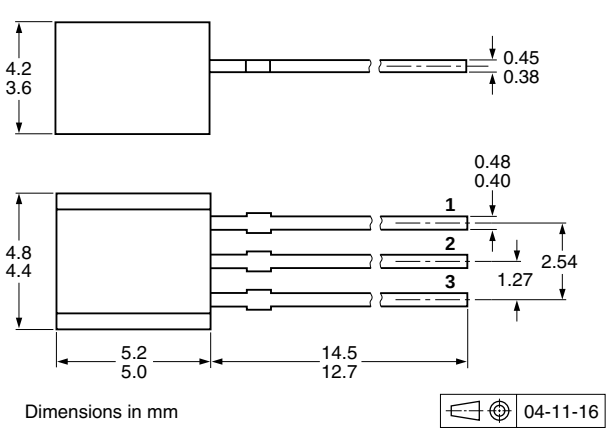


Fig 6. Package outline SOT54 (SC-43A/TO-92)

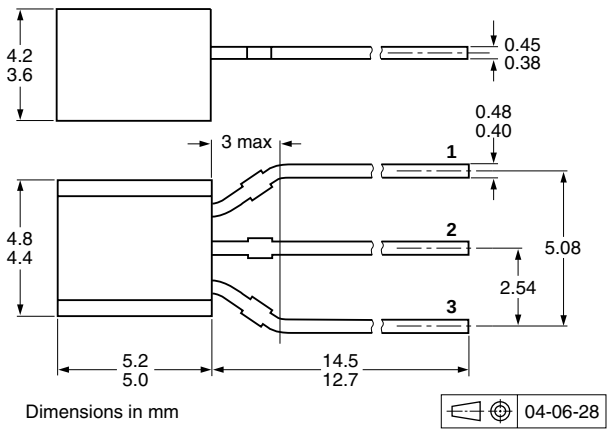


Fig 7. Package outline SOT54A

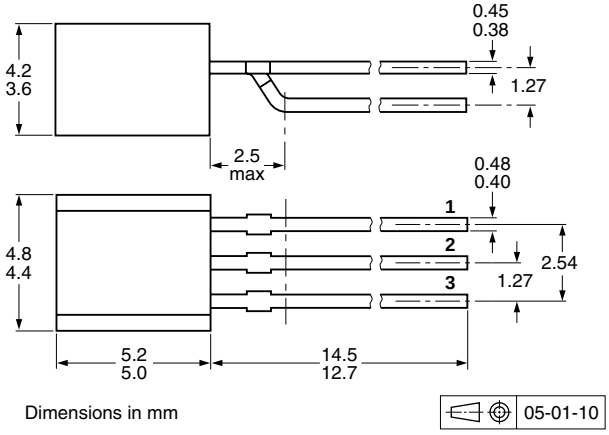


Fig 8. Package outline SOT54 variant

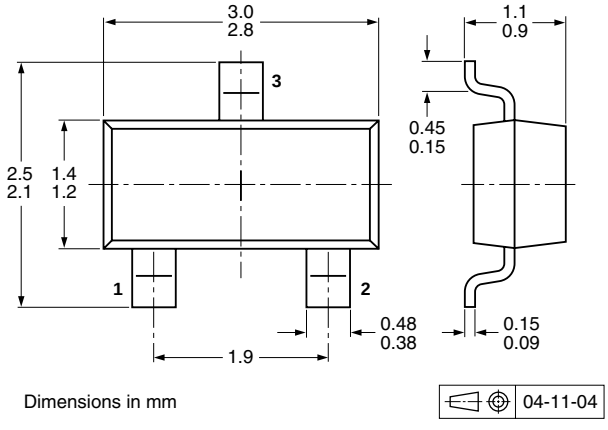


Fig 9. Package outline SOT23 (TO-236AB)

9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity		
			3000	5000	10000
PDTD123EK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-135
PDTD123ES	SOT54	bulk, straight leads	-	-412	-
	SOT54A	tape and reel, wide pitch	-	-	-116
		tape ammopack, wide pitch	-	-	-126
	SOT54 variant	bulk, delta pinning	-	-112	-
PDTD123ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235

[1] For further information and the availability of packing methods, see Section 12.

10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTD123E_SER_2	20091116	Product data sheet	-	PDTD123E_SER_1
Modifications:	• This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.			
PDTD123E_SER_1	20050408	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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13. Contents

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